TOSHIBA TRANSISTOR SILOCON NPN EPITAXIAL TYPE (PCT PROCESS)

2SC732TM

LOW NOISE AUDIO AMPLIFIER APPLICATIONS

High Breakdomn Voltage: VCEO = 50V

Excellent hFE Linearity

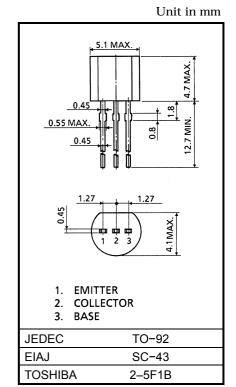
: $h_{FE} (I_C = 0.1 \text{mA})/h_{FE} (I_C = 2 \text{mA}) = 0.95 \text{ (Typ.)}$

• Low Noise : NF (1) = 0.5dB (Typ.) (f = 100Hz)

: NF (2) = 0.2dB (Typ.) (f = 1kHz)

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	60	V
Collector-Emitter Voltage	V_{CEO}	50	V
Emitter-Base Voltage	V _{EBO}	5	V
Collector Current	Ic	150	mA
Base Current	ΙΒ	30	mA
Collector Power Dissipation	P _C	400	mW
Junction Temperature	Tj	125	°C
Storage Temperature Range	T _{stg}	-55~125	°C



Weight: 0.21g

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damage to property.

In developing your designs, please ensure that TOSHIBA products are used within specified operating ranges as set forth in the most recent TOSHIBA products specifications. Also, please keep in mind the precautions and conditions set forth in the "Handling Guide for Semiconductor Devices," or "TOSHIBA Semiconductor Reliability Handbook" etc.

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ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN	TYP.	MAX	UNIT
Collector Cut-off Current	I _{CBO}	V _{CB} = 60V, I _E = 0	_	_	0.1	μΑ
Emitter Cut-off Current	I _{EBO}	V _{EB} = 5V, I _C = 0	_	_	0.1	μΑ
DC Current Gain	h _{FE} (Note)	V _{CE} = 6V, I _C = 2mA	200	_	700	
Collector-Emitter Saturation Voltage	V _{CE (sat)}	I _C = 10mA, I _B = 1mA	_	_	0.3	V
Base-Emitter Voltage	V_{BE}	V _{CE} = 6V, I _C = 2mA	_	0.65	_	V
Transition Frequency	f⊤	V _{CE} = 6V, I _C = 1mA	_	150	_	MHz
Collector Output Capacitance	C _{ob}	V _{CB} = 10V, I _E = 0, f = 1MHz	_	2.0	_	pF
Noise Figure	NF (1)	V_{CE} = 6V, I_{C} = 0.1mA, f = 100Hz, R_{G} = 10k Ω	_	0.5	6	V
Noise Figure	NF (2)	V_{CE} = 6V, I_{C} = 0.1mA, f = 1kHz, R _G = 10k Ω	_	0.2	3	V

Note: hFE Classification GR: 200~400, BL: 350~600

